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Form 1449*	Atty. Docket No.: 303.389US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
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Application Number	09/467992
Filing Date	December 20, 1999
First Named Inventor	Forbes, Leonard
Group Art Unit	2815
Examiner Name	Lee, Eugene

Attorney Docket No: 303.389US2

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